


International  
**IRF** Rectifier

**P100 SERIES**

**PASSIVATED ASSEMBLED CIRCUIT ELEMENTS**

**Features**

- Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 V<sub>RRM</sub>, V<sub>DRM</sub>
- High dynamic characteristics
- Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved 

25A

**Description**

The P100 series of Integrated Power Circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

**Major Ratings and Characteristics**

Parameters	P100	Units
I <sub>D</sub>	25	A
@ T <sub>C</sub>	85	°C
I <sub>FSM</sub>	357	A
@ 50Hz	375	A
@ 60Hz	637	A <sup>2</sup> s
I <sup>2</sup> t	580	A <sup>2</sup> s
@ 50Hz	6365	A <sup>2</sup> √s
@ 60Hz		
V <sub>RRM</sub>	400 to 1200	V
V <sub>INS</sub>	2500	V
T <sub>J</sub>	- 40 to 125	°C

## P100 Series

Bulletin I27125 rev. A 04/99

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### ELECTRICAL SPECIFICATIONS

#### Voltage Ratings

Type number	$V_{RRM}$ maximum repetitive peak reverse voltage V	$V_{RSM}$ maximum non-repetitive peak reverse voltage V	$V_{DRM}$ maximum repetitive peak off-state voltage V	$I_{RRM}$ max. @ $T_J$ max. mA
P101, P121, P131	400	500	400	10
P102, P122, P132	600	700	600	
P103, P123, P133	800	900	800	
P104, P124, P134	1000	1100	1000	
P105, P125, P135	1200	1300	1200	

#### On-state Conduction

Parameter	P100	Units	Conditions
$I_D$ Maximum DC output current	25	A	@ $T_C = 85^\circ\text{C}$ , full bridge
$I_{TSM}$ Max. peak one-cycle non-repetitive on-state or forward current	357	A	t = 10ms No voltage
$I_{FSM}$	375		t = 8.3ms reapplied
	300		t = 10ms 100% $V_{RRM}$
	315		t = 8.3ms reapplied
$I^2t$ Maximum $I^2t$ for fusing	637	A <sup>2</sup> s	t = 10ms No voltage
	580		t = 8.3ms reapplied
	450		t = 10ms 100% $V_{RRM}$
	410		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	6365	A <sup>2</sup> √s	t = 0.1 to 10ms, no voltage reapplied $I^2t$ for time tx = $I^2\sqrt{t} \cdot \sqrt{tx}$
$V_{T(TO)}$ Max. value of threshold voltage	0.82	V	$T_J = 125^\circ\text{C}$
$r_{t1}$ Max. level value of on-state slope resistance	12	mΩ	$T_J = 125^\circ\text{C}$ , Av. power = $V_{T(TO)} \cdot I_{T(AV)} + r_t + (I_{T(RMS)})^2$
$V_{TM}$ Max. peak on-state or forward voltage drop	1.35	V	$T_J = 25^\circ\text{C}$ , $I_{TM} = \pi \times I_{T(AV)}$
di/dt Maximum non repetitive rate of rise of turned on current	200	A/μs	$T_J = 125^\circ\text{C}$ from 0.67 $V_{DRM}$ $I_{TM} = \pi \times I_{T(AV)}$ , $I_g = 500\text{mA}$ , tr < 0.5μs, tp > 6μs
$I_H$ Maximum holding current	130	mA	$T_J = 25^\circ\text{C}$ anode supply = 6V, resistive load, gate open
$I_L$ Maximum latching current	250	mA	$T_J = 25^\circ\text{C}$ anode supply = 6V, resistive load

**Blocking**

Parameter	P100	Units	Conditions
$dv/dt$ Maximum critical rate of rise of off-state voltage	200	V/ $\mu$ s	$T_J = 125^\circ\text{C}$ , exponential to $0.67 V_{\text{DRM}}$ gate open
$I_{\text{RRM}}$ Max. peak reverse and off-state leakage current at $V_{\text{RRM}}, V_{\text{DRM}}$	10	mA	$T_J = 125^\circ\text{C}$ , gate open circuit
$I_{\text{RRM}}$ Max peak reverse leakage current	100	$\mu$ A	$T_J = 25^\circ\text{C}$
$V_{\text{INS}}$ RMS isolation voltage	2500	V	50Hz, circuit to base, all terminal shorted, $T_J = 25^\circ\text{C}$ , $t = 1\text{s}$

**Triggering**

Parameter	P100	Units	Conditions	
$P_{\text{GM}}$ Maximum peak gate power	8	W		
$P_{\text{G(AV)}}$ Maximum average gate power	2			
$I_{\text{GM}}$ Maximum peak gate current	2	A		
$-V_{\text{GM}}$ Maximum peak negative gate voltage	10	V	Anode Supply = 6V resistive load	
$V_{\text{GT}}$ Maximum gate voltage required to trigger	3			$T_J = -40^\circ\text{C}$
	2			$T_J = 25^\circ\text{C}$
	1	$T_J = 125^\circ\text{C}$		
$I_{\text{GD}}$ Maximum gate current required to trigger	90	mA	Anode Supply = 6V resistive load	
	60			$T_J = -40^\circ\text{C}$
	35			$T_J = 125^\circ\text{C}$
$V_{\text{GD}}$ Maximum gate voltage that will not trigger	0.2	V	$T_J = 125^\circ\text{C}$ , rated $V_{\text{DRM}}$ applied	
$I_{\text{GD}}$ Maximum gate current that will not trigger	2	mA	$T_J = 125^\circ\text{C}$ , rated $V_{\text{DRM}}$ applied	

**Thermal and Mechanical Specification**

Parameter	P100	Units	Conditions
$T_J$ Max. operating temperature range	-40 to 125	$^\circ\text{C}$	
$T_{\text{stg}}$ Max. storage temperature range	-40 to 125		
$R_{\text{thJC}}$ Max. thermal resistance, junction to case	2.24	K/W	DC operation per junction
$R_{\text{thCS}}$ Max. thermal resistance, case to heatsink	0.10	K/W	Mounting surface, smooth and greased
T Mounting torque, base to heatsink	4	Nm	A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound
wt Approximate weight	58 (2.0)	g (oz)	

# P100 Series

Bulletin I27125 rev. A 04/99

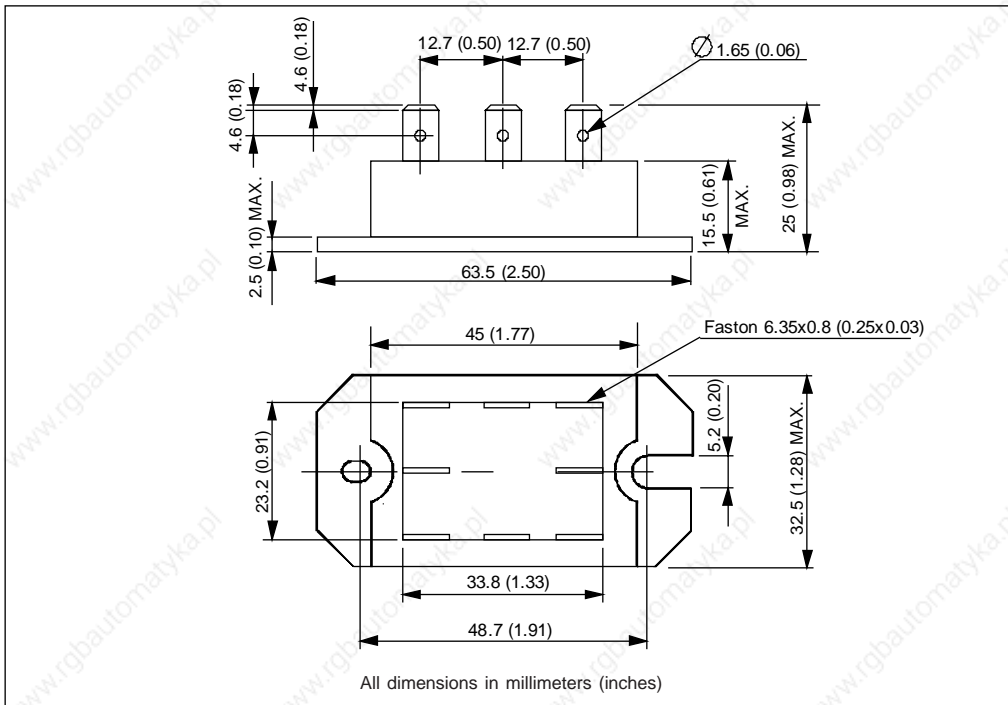
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## Circuit Type and Coding \*

	Circuit"0"	Circuit"2"	Circuit"3"
Terminal Positions			
Schematic diagram			
	SinglePhase HybridBridge CommonCathode	SinglePhase HybridBridge Doubler	SinglePhase AllSCR Bridge
Basic series	P10.	P12.	P13.
With voltage suppression	P10.K	P12.K	P13.K
With free-wheeling diode	P10.W	-	-
With both voltage suppression and free-wheeling diode	P10.KW	-	-

\* To complete code refer to voltage ratings table, i.e.: for 600V P10.W complete code is P102W

## Outline Table



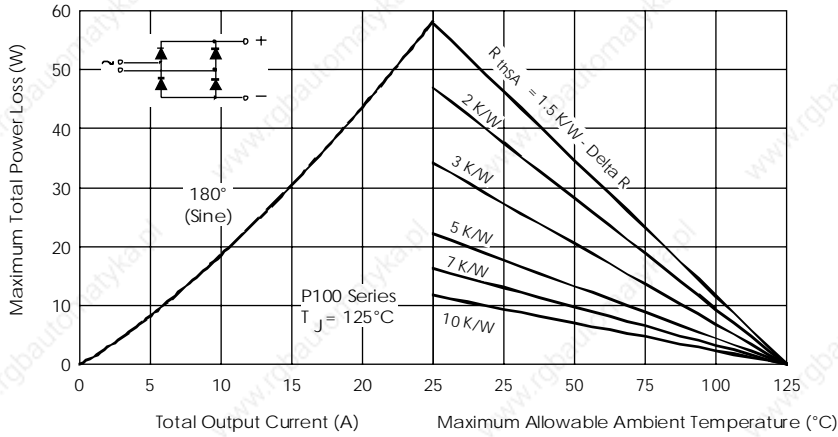


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)

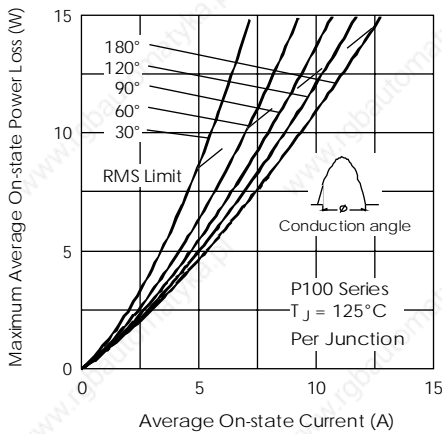


Fig. 2 - On-state Power Loss Characteristics

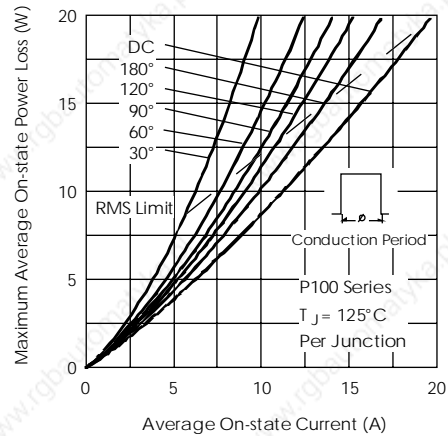


Fig. 3 - On-state Power Loss Characteristics

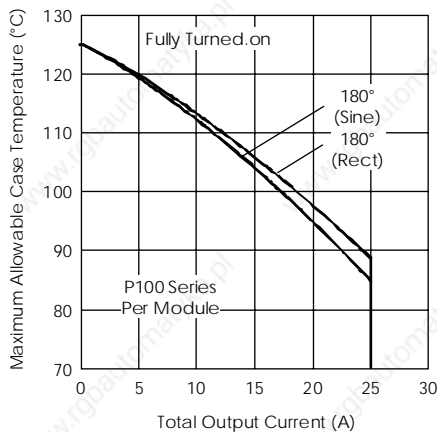


Fig. 4 - Current Ratings Characteristics

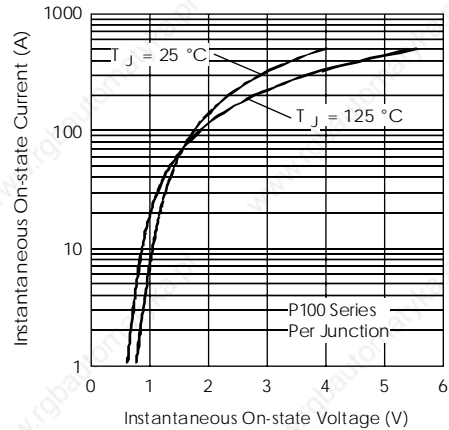


Fig. 5 - On-state Voltage Drop Characteristics

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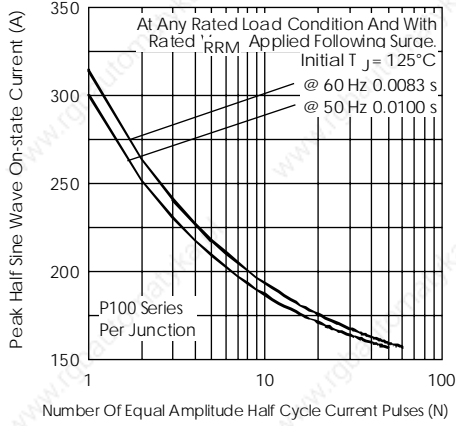


Fig. 6 - Maximum Non-Repetitive Surge Current

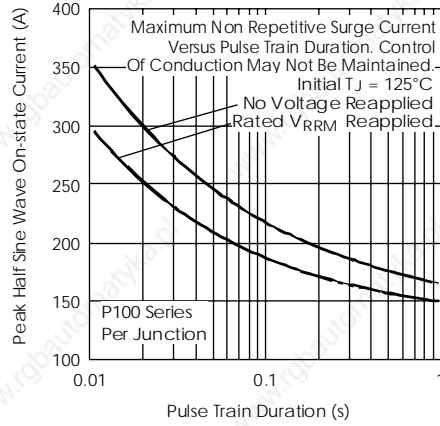


Fig. 7 - Maximum Non-Repetitive Surge Current

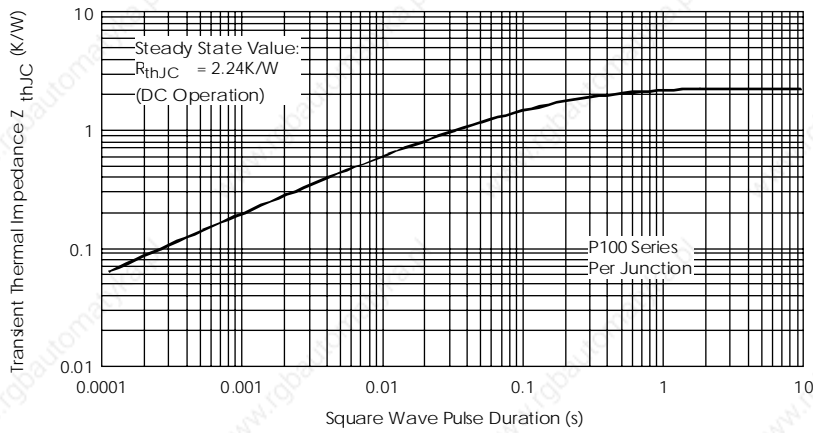


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

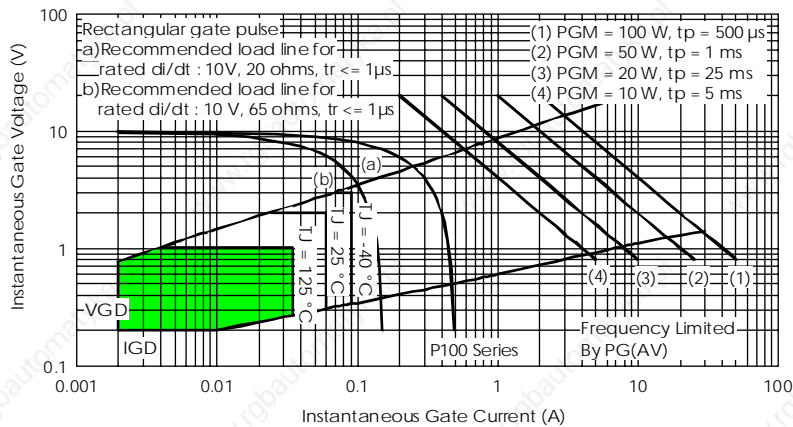


Fig. 9 - Gate Characteristics

